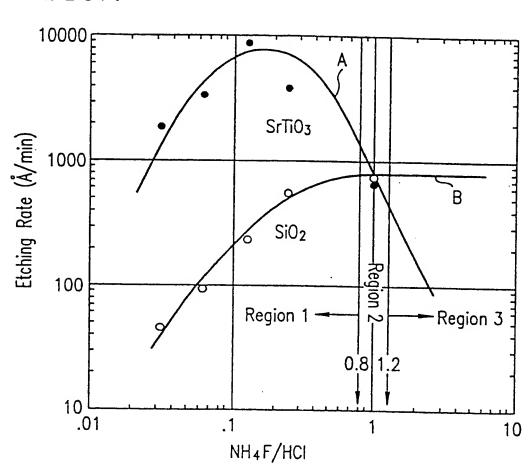
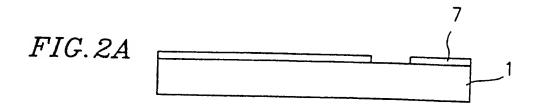
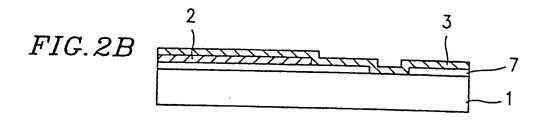
Inventor: Hidetoshi Ishida, et al. Title: Etchant and Method for Fabricating a Semiconductor Device Using the Same Atty. Docket No.: YAO-3990US3 Customer No. 23122 Express Mail No.: EV351885193US

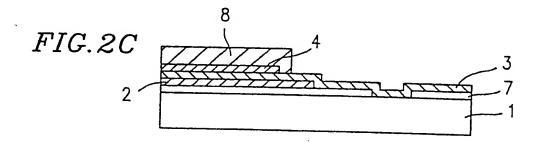


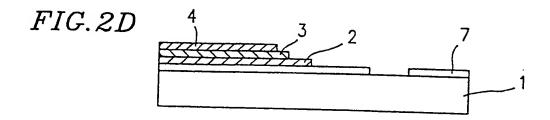


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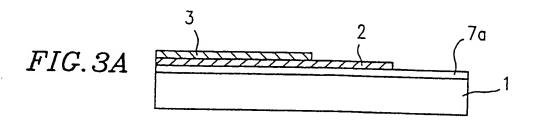


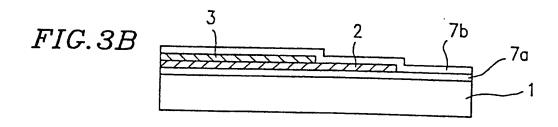


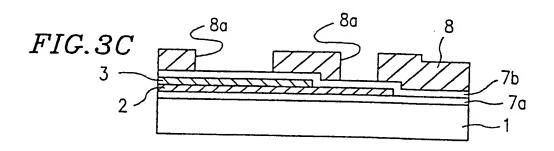


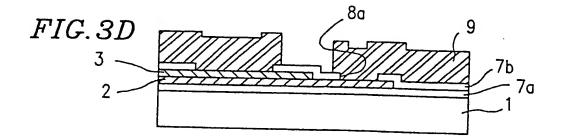


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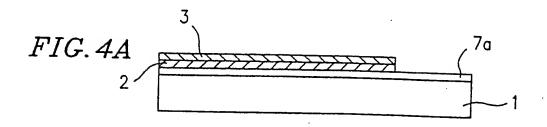


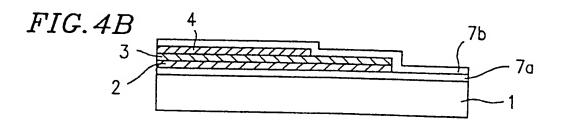


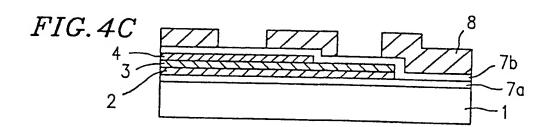


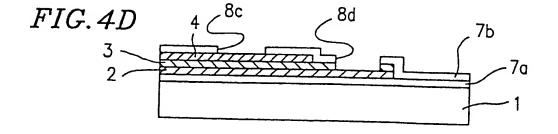


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